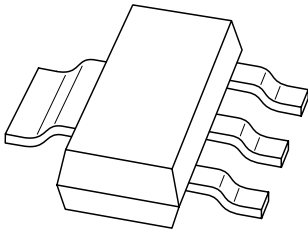


DATA SHEET



PBSS4540Z NPN medium power transistor

Preliminary specification

1999 Aug 04

NPN medium power transistor

PBSS4540Z

FEATURES

- High current (max. 10 A)
- Low voltage (max. 40 V)
- Low V_{CEsat} .

APPLICATIONS

- Heavy duty battery powered equipment (Automotive, Telecom and Audio/Video) such as motor and lamp drivers
- V_{CEsat} critical applications such as the latest low supply voltage IC applications
- All battery driven equipment to save battery power.

DESCRIPTION

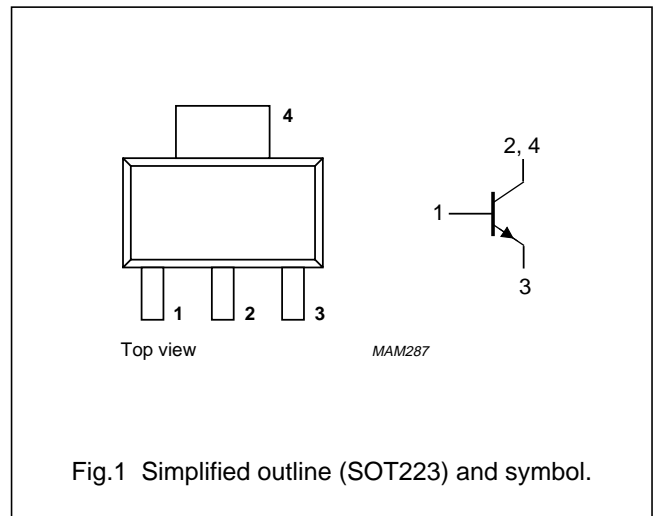
NPN low V_{CEsat} transistor in a SOT223 plastic package. PNP complement: PBSS5540Z.

MARKING CODE

TYPE NUMBER	MARKING CODE
PBSS4540Z	PB4540

PINNING

PIN	DESCRIPTION
1	base
2	collector
3	emitter
4	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	40	V
V_{CEO}	collector-emitter voltage	open base	–	40	V
V_{EBO}	emitter-base voltage	open collector	–	6	V
I_C	collector current (DC)		–	5	A
I_{CM}	peak collector current		–	10	A
I_{BM}	peak base current		–	2	A
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$; note 1	–	1.35	W
T_{stg}	storage temperature		–65	+150	$^\circ\text{C}$
T_j	junction temperature		–	150	$^\circ\text{C}$
T_{amb}	operating ambient temperature		–65	+150	$^\circ\text{C}$

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see “Thermal considerations for SOT223 in the General Part of associated Handbook”.

NPN medium power transistor

PBSS4540Z

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	92	K/W

Note

1. Device mounted on a printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm². For other mounting conditions, see "Thermal considerations for SOT223 in the General Part of associated Handbook".

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	$I_E = 0; V_{CB} = 30\text{ V}$	–	–	100	nA
		$I_E = 0; V_{CB} = 30\text{ V}; T_j = 150\text{ °C}$	–	–	50	μA
I_{EBO}	emitter cut-off current	$I_C = 0; V_{EB} = 5\text{ V}$	–	–	100	nA
h_{FE}	DC current gain	$V_{CE} = 2\text{ V}$ $I_C = 500\text{ mA}$	300	500	–	
		$I_C = 1\text{ A}; \text{note 1}$	300	500	–	
		$I_C = 2\text{ A}; \text{note 1}$	250	450	–	
		$I_C = 5\text{ A}; \text{note 1}$	50	150	–	
V_{CEsat}	saturation voltage	$I_C = 500\text{ mA}; I_B = 5\text{ mA}$	–	65	120	mV
		$I_C = 1\text{ A}; I_B = 10\text{ mA}$	–	100	150	mV
		$I_C = 2\text{ A}; I_B = 200\text{ mA}; \text{note 1}$	–	130	170	mV
		$I_C = 5\text{ A}; I_B = 500\text{ mA}; \text{note 1}$	–	300	400	mV
V_{BEsat}	saturation voltage	$I_C = 5\text{ A}; I_B = 500\text{ mA}; \text{note 1}$	–	1.1	1.3	V
V_{BEon}	base-emitter turn-on voltage	$I_C = 2\text{ A}; V_{CE} = 2\text{ V}$	1.1	0.8	–	V
C_c	collector capacitance	$I_E = i_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	60	70	pF
f_T	transition frequency	$I_C = 500\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$	80	120	–	MHz

Note

1. Pulse test: $t_p \leq 300\text{ μs}; \delta \leq 0.02$.

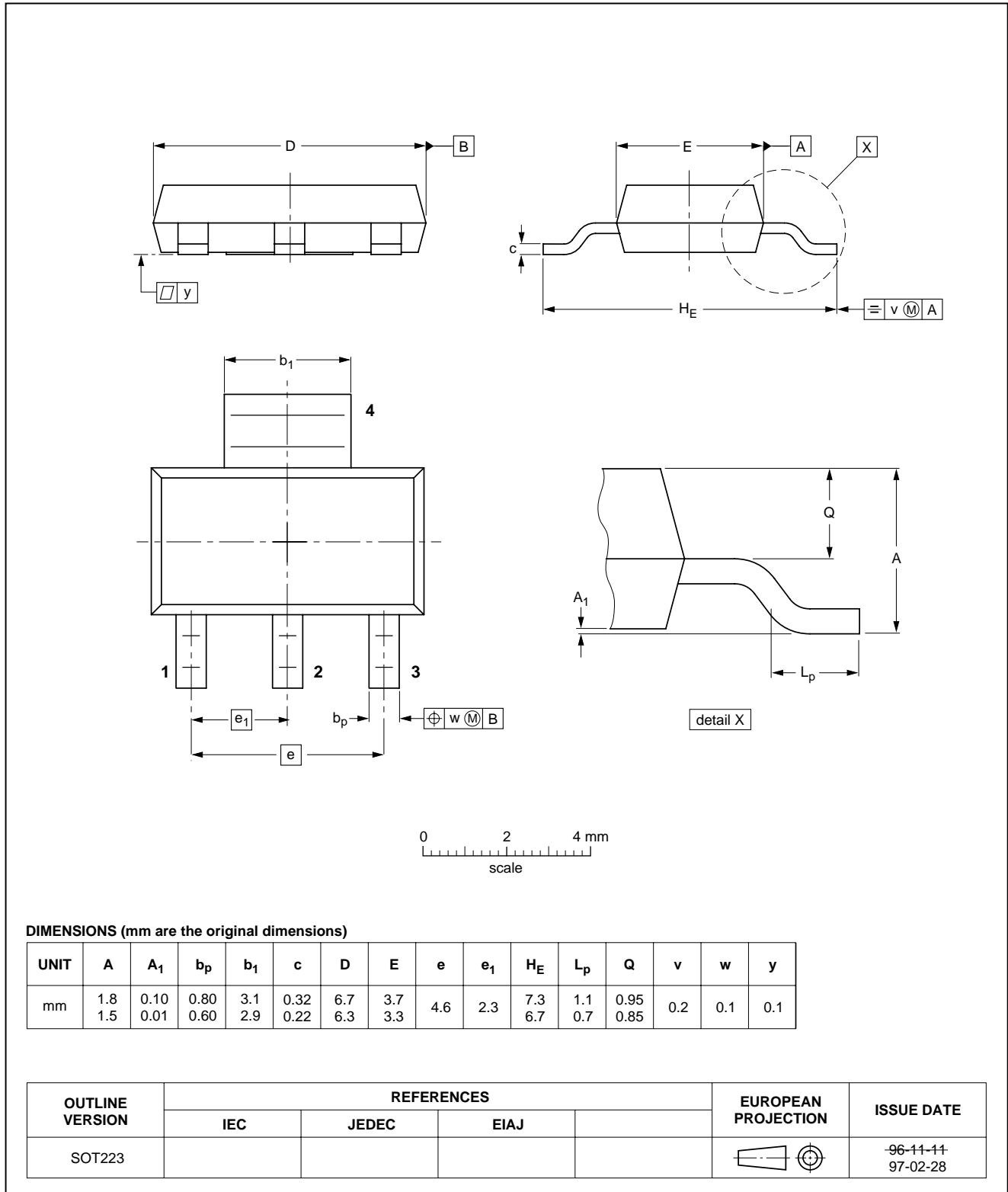
NPN medium power transistor

PBSS4540Z

PACKAGE OUTLINE

Plastic surface mounted package; collector pad for good heat transfer; 4 leads

SOT223



NPN medium power transistor

PBSS4540Z

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices, or systems where malfunction of these products can reasonably be expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.

NPN medium power transistor

PBSS4540Z

NOTES

NPN medium power transistor

PBSS4540Z

NOTES

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